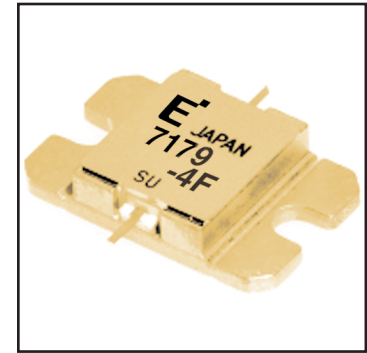


FEATURES

- High Output Power: $P_{1dB} = 36.5\text{dBm}$ (Typ.)
- High Gain: $G_{1dB} = 9.0\text{dB}$ (Typ.)
- High PAE: $\eta_{add} = 35\%$ (Typ.)
- Low $IM_3 = -46\text{dBc}$ @ $P_o = 25.5\text{dBm}$
- Broad Band: 7.1 ~ 7.9GHz
- Impedance Matched $Z_{in}/Z_{out} = 50\Omega$
- Hermetically Sealed Package

DESCRIPTION

The FLM7179-4F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.



Eudyna's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25^\circ\text{C}$)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	$T_c = 25^\circ\text{C}$	25.0	W
Storage Temperature	T_{stg}		-65 to +175	$^\circ\text{C}$
Channel Temperature	T_{ch}		175	$^\circ\text{C}$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 16.0 and -2.2 mA respectively with gate resistance of 100 Ω .

ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^\circ\text{C}$)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I_{DSS}	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V}$	-	1700	2600	mA
Transconductance	g_m	$V_{DS} = 5\text{V}, I_{DS} = 1100\text{mA}$	-	1700	-	mS
Pinch-off Voltage	V_p	$V_{DS} = 5\text{V}, I_{DS} = 85\text{mA}$	-0.5	-1.5	-3.0	V
Gate Source Breakdown Voltage	V_{GSO}	$I_{GS} = -85\mu\text{A}$	-5.0	-	-	V
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS} = 10\text{V},$ $I_{DS} = 0.65 I_{DSS}$ (Typ.), $f = 7.1 \sim 7.9\text{GHz},$ $Z_S = Z_L = 50\text{ohm}$	35.5	36.5	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}		8.0	9.0	-	dB
Drain Current	I_{dsr}		-	1100	1300	mA
Power-added Efficiency	η_{add}		-	35	-	%
Gain Flatness	ΔG		-	-	± 0.6	dB
3rd Order Intermodulation Distortion	IM_3	$f = 7.9\text{GHz}, \Delta f = 10\text{MHz}$ 2-Tone Test $P_{out} = 25.5\text{dBm S.C.L.}$	-44	-46	-	dBc
Thermal Resistance	R_{th}	Channel to Case	-	5.0	6.0	$^\circ\text{C/W}$
Channel Temperature Rise	ΔT_{ch}	$10\text{V} \times I_{dsr} \times R_{th}$	-	-	80	$^\circ\text{C}$

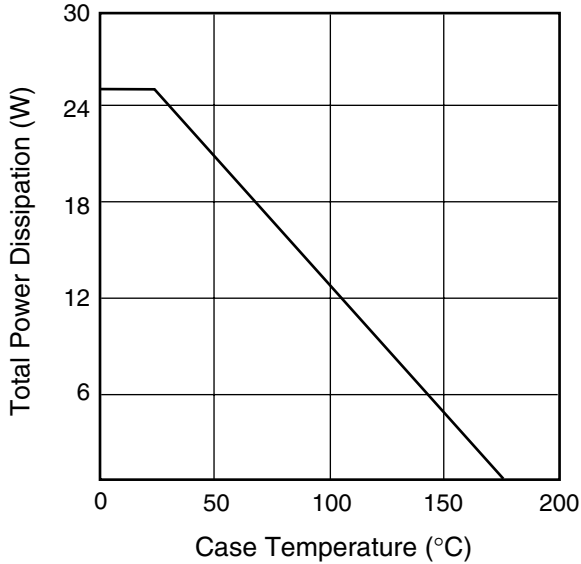
CASE STYLE: IB

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

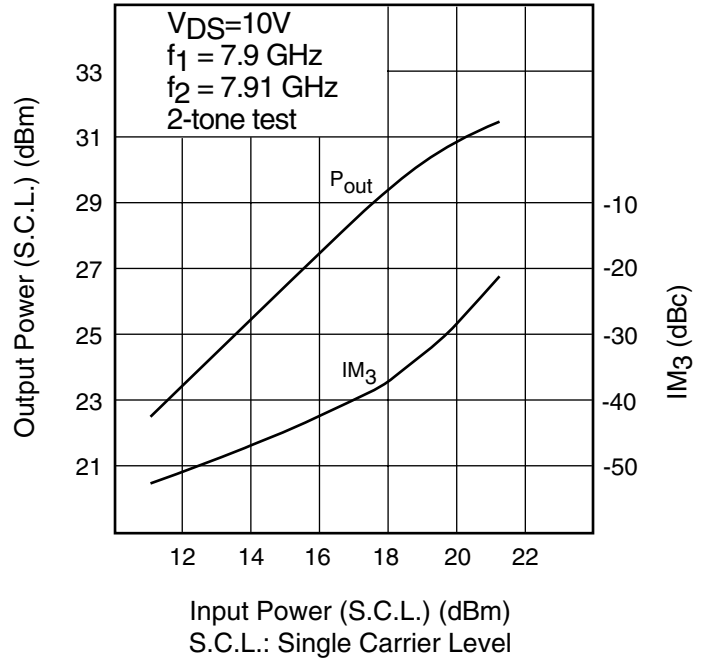
FLM7179-4F

C-Band Internally Matched FET

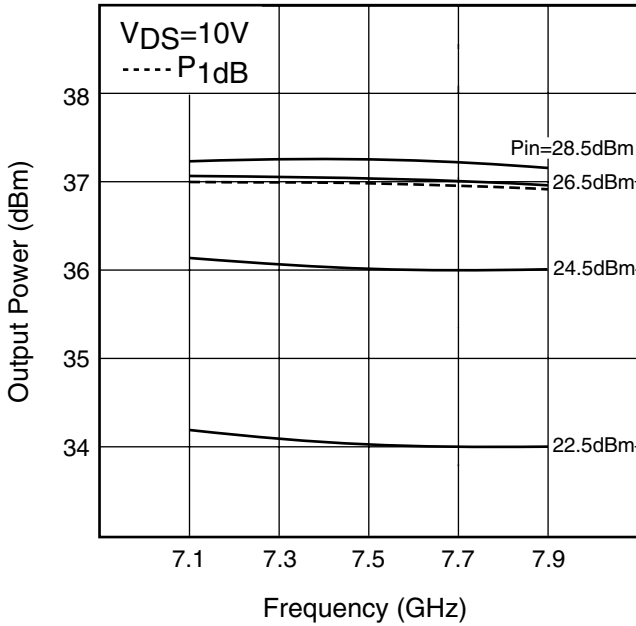
POWER DERATING CURVE



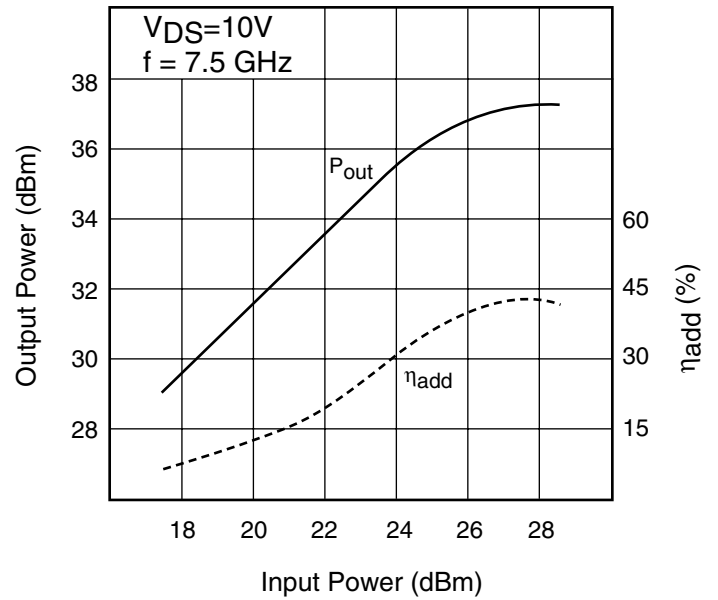
OUTPUT POWER & IM₃ vs. INPUT POWER

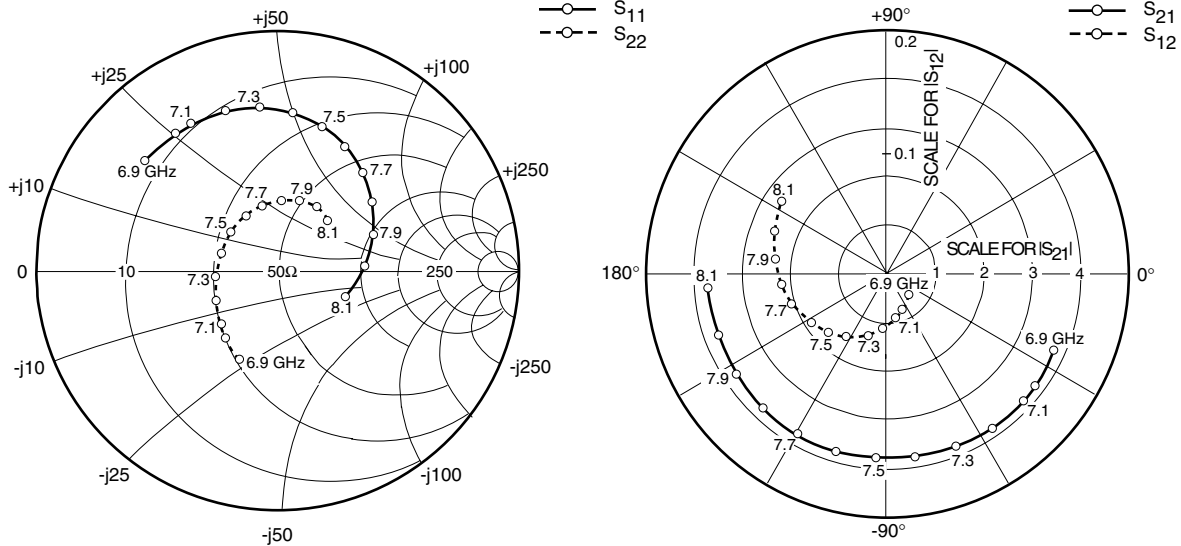


OUTPUT POWER vs. FREQUENCY



OUTPUT POWER vs. INPUT POWER





S-PARAMETERS

$V_{DS} = 10V, I_{DS} = 1100mA$

FREQUENCY (MHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
6900	.712	140.3	3.823	-24.3	.025	-45.8	.402	-113.7
7000	.714	127.0	3.840	-37.1	.032	-67.6	.354	-127.8
7100	.710	120.5	3.850	-42.7	.036	-77.9	.324	-136.3
7200	.701	108.1	3.852	-55.5	.045	-93.2	.288	-154.2
7300	.684	96.2	3.831	-68.0	.053	-106.9	.259	-175.1
7400	.658	84.6	3.820	-80.9	.061	-122.3	.249	162.0
7500	.625	73.0	3.804	-93.5	.068	-135.6	.251	140.4
7600	.584	61.4	3.783	-106.3	.075	-148.9	.262	120.3
7700	.535	49.2	3.768	-119.4	.082	-162.2	.275	102.2
7800	.481	36.1	3.756	-132.6	.088	-174.2	.295	86.7
7900	.421	20.8	3.744	-146.1	.093	172.4	.307	72.3
8000	.359	2.3	3.726	-160.0	.100	159.7	.305	59.4
8100	.300	-22.5	3.708	-174.9	.106	145.5	.293	45.9